

NCE P-Channel Super Trench Power MOSFET

Description

The NCEP40PT12K uses **Super Trench** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{DS(ON)}$ and Q_g . This device is ideal for high-frequency switching and synchronous rectification

Application

- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

General Features

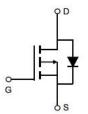
- V_{DS} =-40V, I_{D} =-120A $R_{DS(ON)}$ =4.55mΩ (typical) @ V_{GS} =-10V $R_{DS(ON)}$ =7.0mΩ (typical) @ V_{GS} =-4.5V
- Excellent gate charge x R_{DS(on)} product(FOM)
- Very low on-resistance R_{DS(on)}
- 175 °C operating temperature
- Pb-free lead plating

100% UIS TESTED! 100% ΔVds TESTED!

TO-252-2L







Schematic Diagram

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCEP40PT12K	NCEP40PT12K	TO-252-2L	Ø330mm	16mm	2500units

Absolute Maximum Ratings (T_c=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	VDS	-40	V
Gate-Source Voltage	Vgs	±20	V
Drain Current-Continuous	I _D	-120	А
Drain Current-Continuous(T _C =100 °C)	I _D (100℃)	-84	Α
Pulsed Drain Current	I _{DM}	-480	Α
Maximum Power Dissipation	P _D	220	W
Derating factor		1.47	W/°C
Single pulse avalanche energy (Note 1)	E _{AS}	1155	mJ
Operating Junction and Storage Temperature Range	T_{J}, T_{STG}	-55 To 175	$^{\circ}$ C

Thermal Characteristic

Thermal Resistance,Junction-to-Case	R _{θJC}	0.68	°C/W	
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NCEP40PT12K

Electrical Characteristics (T_C=25 ℃ unless otherwise noted)

$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	-40 - - -1.0 - - -	-1.6 4.55 7.0 50	- 1 ±100 -2.5 5.45 8.5 -	V μA nA V mΩ mΩ S
Zero Gate Voltage Drain Current I_{DSS} $V_{DS}=-40V, V_{GS}=0V$ Gate-Body Leakage Current I_{GSS} $V_{GS}=\pm 20V, V_{DS}=0V$ On CharacteristicsGate Threshold Voltage $V_{GS}(th)$ $V_{DS}=V_{GS}, I_{D}=-250\mu A$ Drain-Source On-State Resistance $P_{DS}(ON)$ $P_{DS}=-10V, I_{D}=-20A$ Forward Transconductance $P_{DS}=-10V, I_{D}=-20A$ Dynamic CharacteristicsInput Capacitance $P_{DS}=-10V, I_{D}=-20V, I_{D}=-$	-1.0	-1.6 4.55 7.0 50	1 ±100 -2.5 5.45 8.5	μΑ nA V mΩ mΩ S
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	-1.0	-1.6 4.55 7.0 50	±100 -2.5 5.45 8.5	nA V mΩ mΩ S
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	-1.0	-1.6 4.55 7.0 50	-2.5 5.45 8.5	V mΩ mΩ S
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	-	4.55 7.0 50	5.45 8.5	mΩ mΩ S
$\begin{array}{c} \text{Drain-Source On-State Resistance} & R_{\text{DS(ON)}} & V_{\text{GS}}\text{=-}10\text{V}, \ I_{\text{D}}\text{=-}20\text{A} \\ \hline V_{\text{GS}}\text{=-}4.5\text{V}, \ I_{\text{D}}\text{=-}20\text{A} \\ \hline V_{\text{DS}}\text{=-}4.5\text{V}, \ I_{\text{D}}\text{=-}20\text{A} \\ \hline \\ \text{Porward Transconductance} & g_{\text{FS}} & V_{\text{DS}}\text{=-}5\text{V}, I_{\text{D}}\text{=-}40\text{A} \\ \hline \\ \text{Dynamic Characteristics} \\ \hline \\ \text{Input Capacitance} & C_{\text{Iss}} & \\ \hline \\ \text{Output Capacitance} & C_{\text{oss}} & \\ \hline \\ \text{Reverse Transfer Capacitance} & C_{\text{rss}} \\ \hline \\ \text{Switching Characteristics} & (\text{Note 2}) \\ \hline \\ \text{Turn-on Delay Time} & t_{\text{d(on)}} & \\ \hline \\ \text{Turn-on Rise Time} & t_{\text{d(off)}} & V_{\text{DD}}\text{=-}20\text{V}, I_{\text{D}}\text{=-}20\text{A} \\ \hline \\ \text{Turn-Off Delay Time} & t_{\text{d(off)}} & V_{\text{GS}}\text{=-}10\text{V}, R_{\text{G}}\text{=}1.6\Omega \\ \hline \\ \text{Turn-Off Fall Time} & t_{\text{f}} & \\ \hline \end{array}$	-	4.55 7.0 50	5.45 8.5	mΩ mΩ S
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$		7.0 50	8.5	mΩ S
Forward Transconductance g_{FS} $V_{DS}=-4.5V$, $I_{D}=-20A$ Dynamic Characteristics Input Capacitance C_{ISS} Output Capacitance C_{OSS} Reverse Transfer Capacitance C_{rSS} Switching Characteristics (Note 2) Turn-on Delay Time $t_{d(on)}$ Turn-on Rise Time $t_{d(off)}$ Turn-Off Delay Time $t_{d(off)}$ Turn-Off Fall Time t_{f}		50 6100	-	S
		6100		
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	-		-	PF
$\begin{array}{cccccccccccccccccccccccccccccccccccc$	-		-	PF
	-	1500		
		1500	-	PF
$ \begin{array}{cccccccccccccccccccccccccccccccccccc$	-	95	-	PF
$\begin{array}{cccccccccccccccccccccccccccccccccccc$				
$\begin{array}{ccc} \text{Turn-Off Delay Time} & & & & & \\ & & & & & \\ \text{Turn-Off Fall Time} & & & & \\ & & & & & \\ \end{array}$	-	13	-	nS
Turn-Off Fall Time t _f	-	30	-	nS
·	-	75	-	nS
T + 1 0 + 0	-	14	-	nS
Total Gate Charge Q _g	-	86	-	nC
Gate-Source Charge Q_{gs} V_{DS} =-20V, I_D =-20A, V_{GS} =-10V	-	17.5		nC
Gate-Drain Charge Q _{gd}	· -			nC
Drain-Source Diode Characteristics	•	•		
Diode Forward Voltage V _{SD} V _{GS} =0V,I _S =-20A	-		-1.2	V
Diode Forward Current Is	-	-	-120	Α
Reverse Recovery Time t_{rr} $T_J = 25^{\circ}C$, $I_F = -60A$	-	55	-	nS
Reverse Recovery Charge Qrr di/dt = 100A/µs		75	-	nC

Notes:

- 1. EAS condition : Tj=25 $^{\circ}\text{C}$,VDD=-20V,VG=-10V,L=0.5mH,Rg=25 Ω
- 2. Guaranteed by design, not subject to production
- 3. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of T_{J(MAX)}=175°C. The SOA curve provides a single pulse rating.



Typical Electrical and Thermal Characteristics

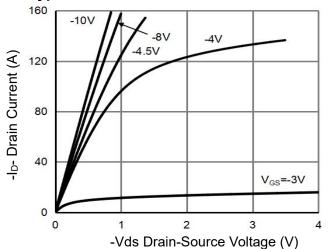


Figure 1 Output Characteristics

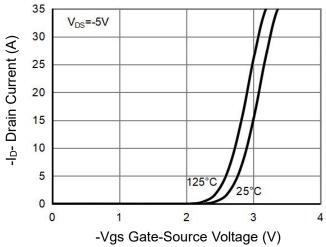


Figure 2 Transfer Characteristics

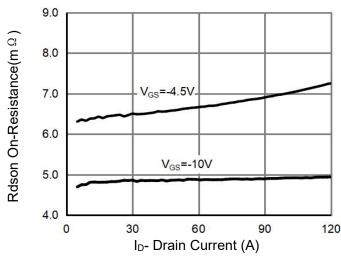


Figure 3 Rdson- Drain Current

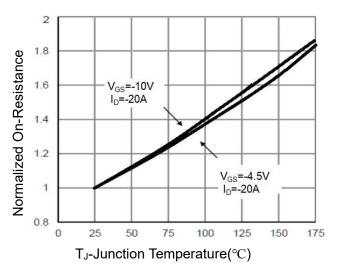


Figure 4 Rdson-JunctionTemperature

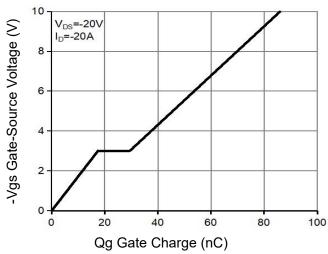


Figure 5 Gate Charge

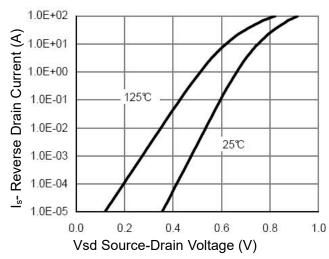


Figure 6 Source- Drain Diode Forward



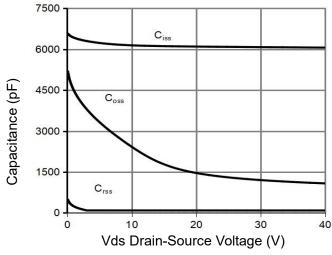


Figure 7 Capacitance vs Vds

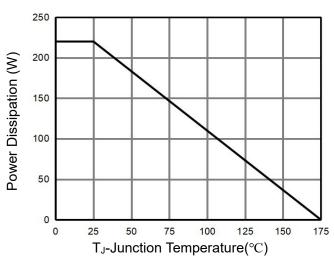


Figure 9 Power De-rating

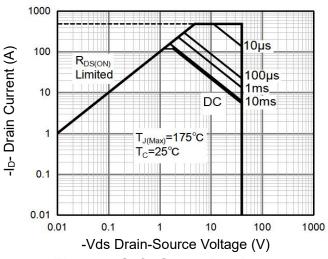


Figure 8 Safe Operation Area(Note3)

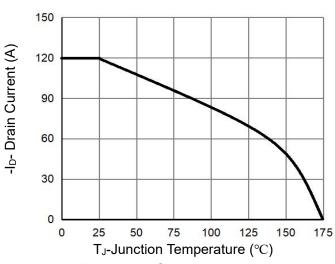


Figure 10 Current De-rating

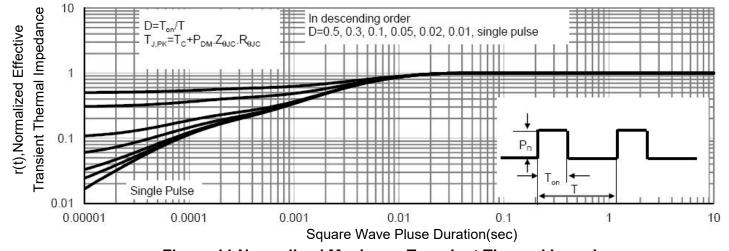
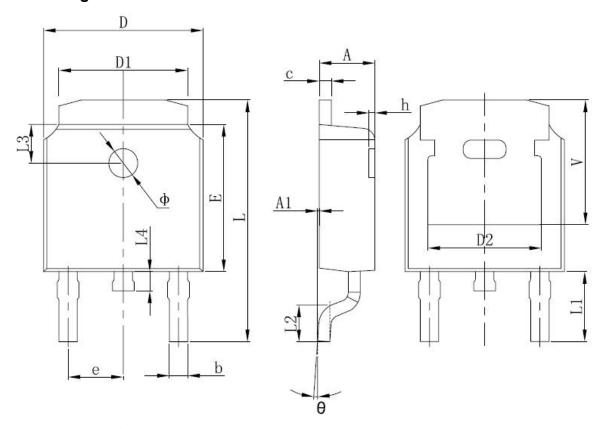


Figure 11 Normalized Maximum Transient Thermal Impedance



TO-252-2L Package Information



Cumbal	Dimensions	In Millimeters	Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
Α	2.200	2.400	0.087	0.094	
A1	0.000	0.127	0.000	0.005	
b	0.635	0.770	0.025	0.030	
С	0.460	0.580	0.018	0.023	
D	6.500	6.700	0.256	0.264	
D1	5.100	5.460	0.201	0.215	
D2	4.830	REF.	0.190 REF.		
E	6.000	6.200	0.236	0.244	
е	2.186	2.386	0.086	0.094	
L	9.712	10.312	0.382	0.406	
L1	2.900	2.900 REF.		REF.	
L2	1.400	1.700	0.055	0.067	
L3	1.600	1.600 REF.		REF.	
L4	0.600	1.000	0.024	0.039	
Ф	1.100	1.300	0.043	0.051	
θ	0°	8°	0°	8°	
h	0.000	0.300	0.000	0.012	
V	5.250	5.250 REF. 0.207 REF		REF.	

http://www.ncepower.com

NCEP40PT12K

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